Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = +25°C
-60V	115mΩ @ V_{GS} = -10V	-3.2A
	145mΩ @ V_{GS} = -4.5V	-2.5A

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/ Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/quality/product-definitions/**
- **An automotive-compliant part is available under a separate datasheet (DMP6111SSSQ)**

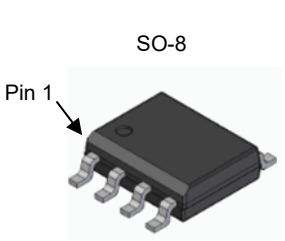
Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

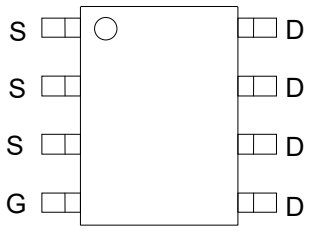
- Backlighting
- Power-management functions
- DC-DC converters

Mechanical Data

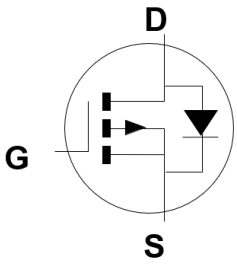
- Package: SO-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.072 grams (Approximate)



Top View



Top View
Pin Configuration



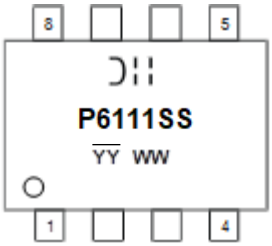
Equivalent Circuit

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMP6111SSS-13	SO-8	2,500	Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



= Manufacturer's Marking
P6111SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year Code (ex: 25 = 2025)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	-60	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current (Note 5) V_{GS} = -10V	T_A = +25°C T_A = +70°C	I_D	-3.2 -2.5	A
Maximum Body Diode Forward Current (Note 5)		I_S	-3.2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	-23	A
Avalanche Current, L = 0.1mH		I_{AS}	-21	A
Avalanche Energy, L = 0.1mH		E_{AS}	22	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)		P_D	1.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	72	°C/W
Total Power Dissipation (Note 5)		P_D	2.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	57	°C/W
Thermal Resistance, Junction to Case (Note 5)	Steady State	$R_{\theta JC}$	7.3	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-60	—	—	V	V_{GS} = 0, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -60V, V_{GS} = 0
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1	—	-3	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	77	115	mΩ	V_{GS} = -10V, I_D = -3A
		—	102	145		V_{GS} = -4.5V, I_D = -3A
Diode Forward Voltage	V_{SD}	—	-0.8	-1.2	V	V_{GS} = 0, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	1286	—	pF	V_{DS} = -30V, V_{GS} = 0 f = 1.0MHz
Output Capacitance	C_{oss}	—	56	—		
Reverse Transfer Capacitance	C_{rss}	—	43	—		
Gate Resistance	R_g	—	5.8	—	Ω	V_{DS} = 0, V_{GS} = 0, f = 1.0MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	11	—	nC	V_{DS} = -30V, I_D = -3A
Total Gate Charge (V_{GS} = -10V)	Q_g	—	23	—		
Gate-Source Charge	Q_{gs}	—	3.7	—		
Gate-Drain Charge	Q_{gd}	—	4.1	—		
Turn-On Delay Time	$t_{D(ON)}$	—	5.3	—	ns	V_{GS} = -10V, V_{DS} = -30V R_{GEN} = 6Ω, I_D = -3A
Turn-On Rise Time	t_R	—	19.3	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	43	—		
Turn-Off Fall Time	t_F	—	21	—		
Reverse-Recovery Time	t_{RR}	—	21	—	ns	I_S = -3A, di/dt = -100A/µs
Reverse-Recovery Charge	Q_{RR}	—	17	—	nC	I_S = -3A, di/dt = -100A/µs

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

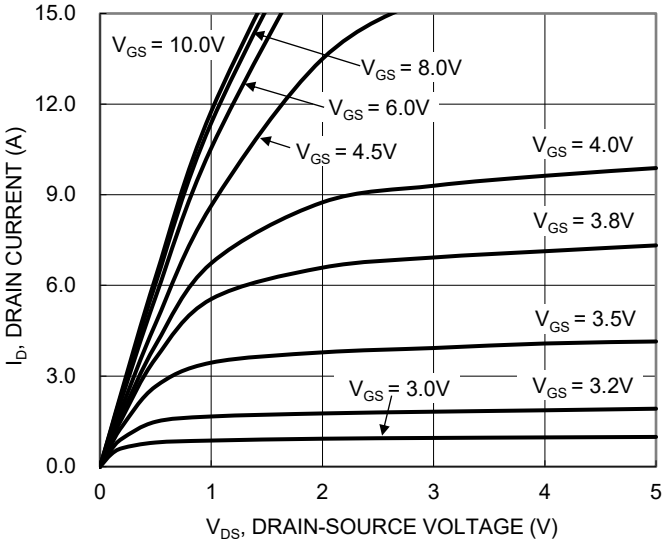


Figure 1. Typical Output Characteristic

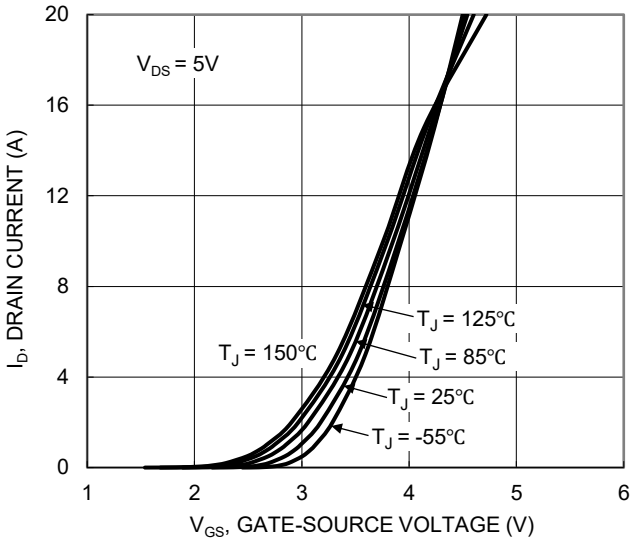


Figure 2. Typical Transfer Characteristic

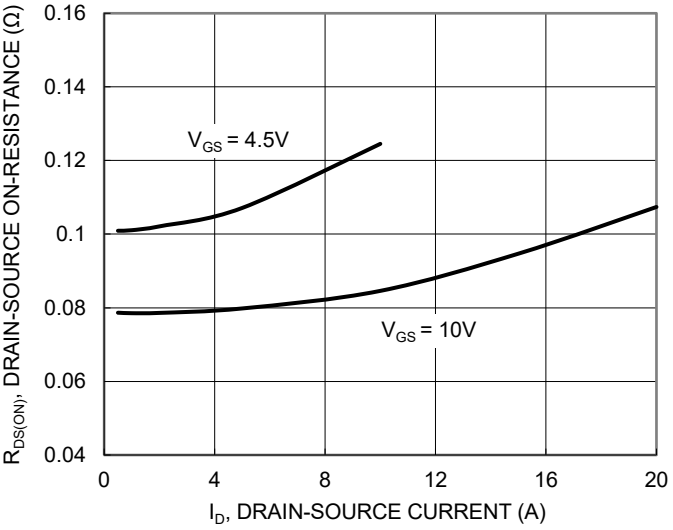


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

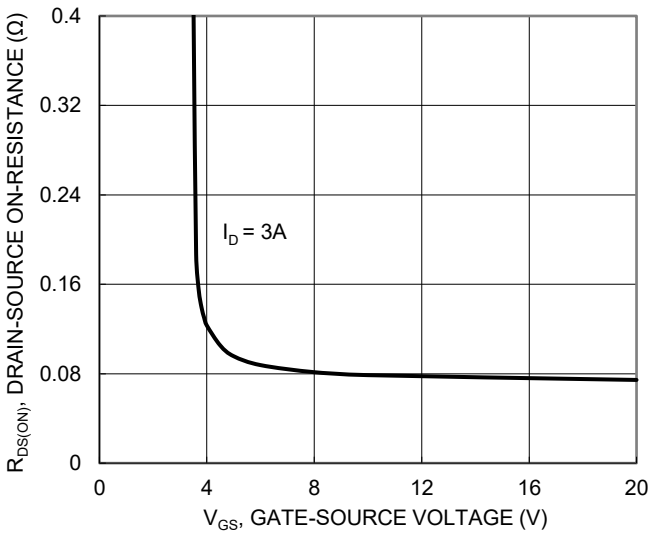


Figure 4. Typical Transfer Characteristic

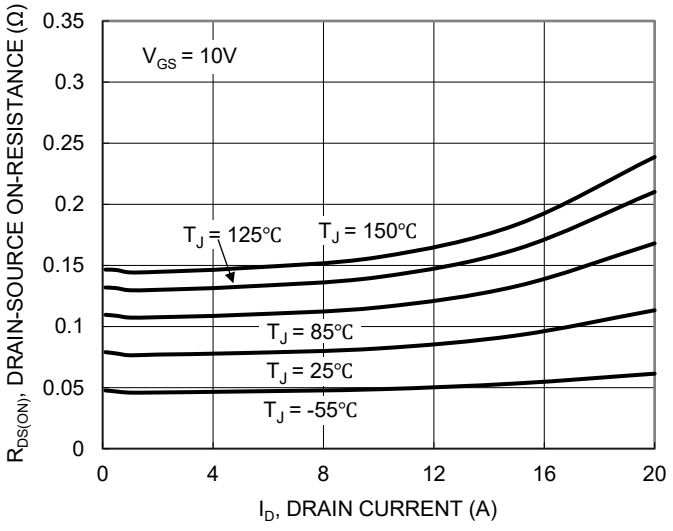


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

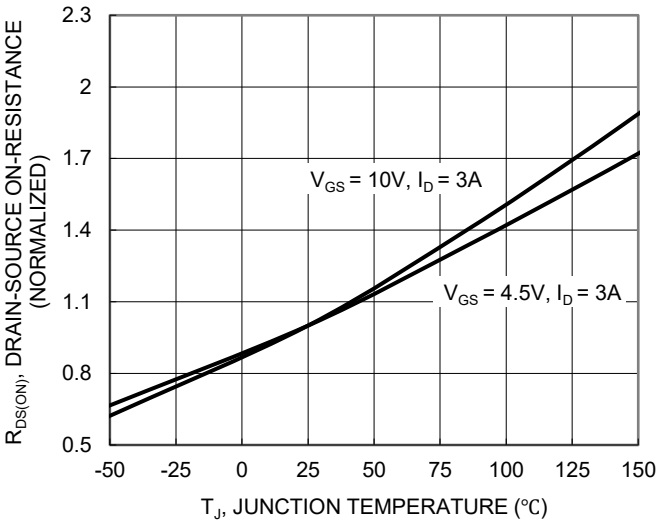


Figure 6. On-Resistance Variation with Junction Temperature

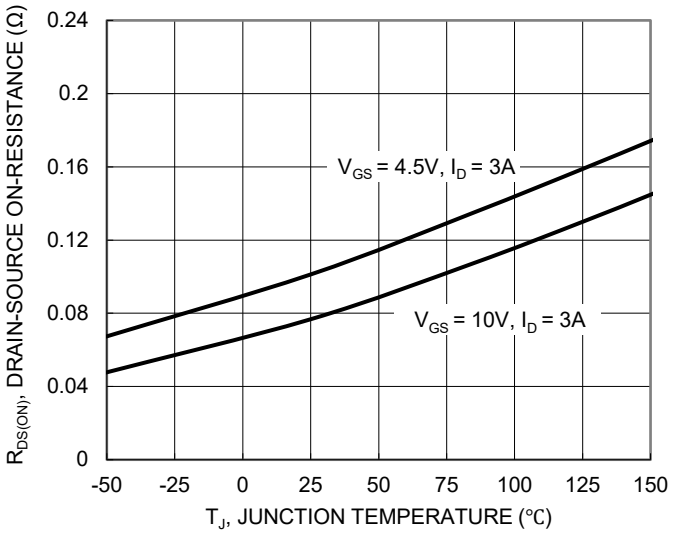


Figure 7. On-Resistance Variation with Junction Temperature

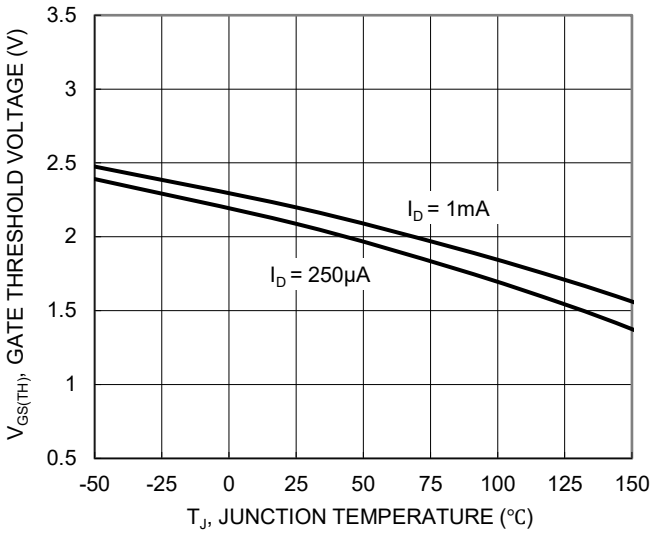


Figure 8. Gate Threshold Variation vs. Junction Temperature

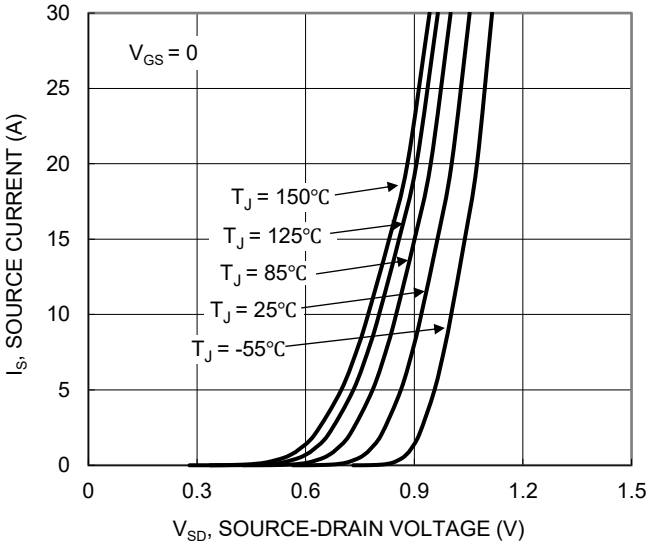


Figure 9. Diode Forward Voltage vs. Current

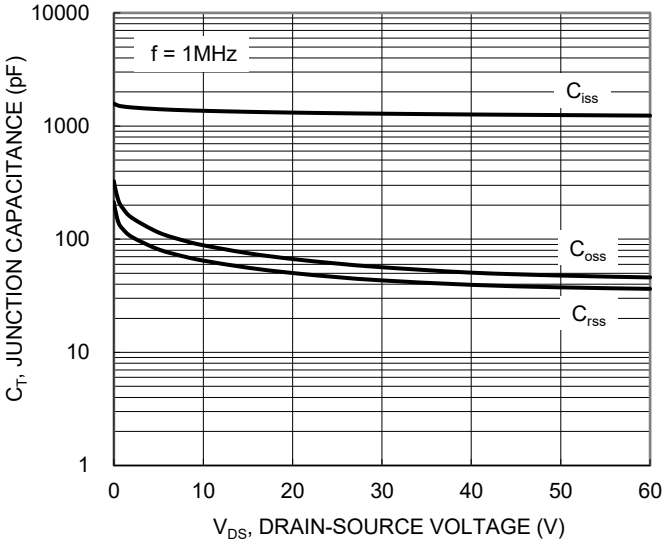


Figure 10. Typical Junction Capacitance

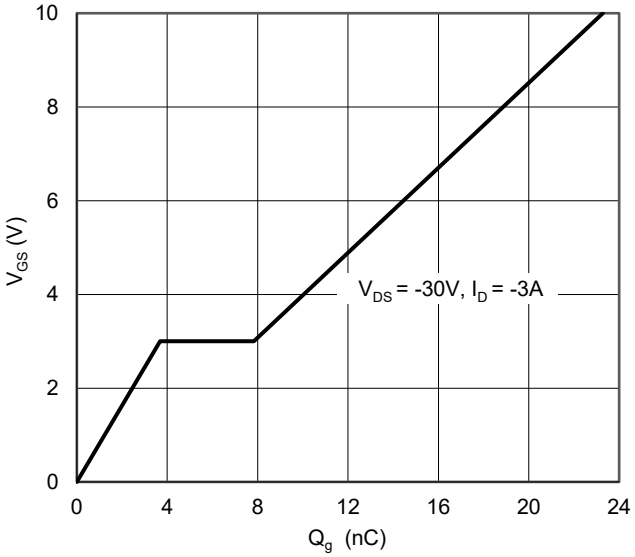


Figure 11. Gate Charge

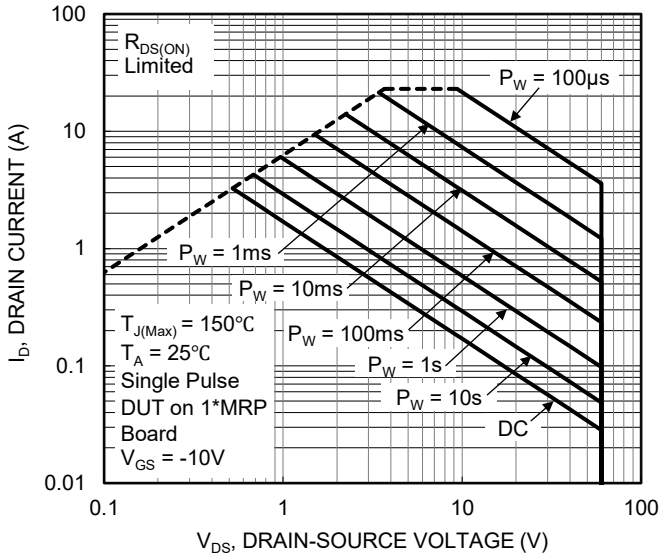


Figure 12. SOA, Safe Operation Area

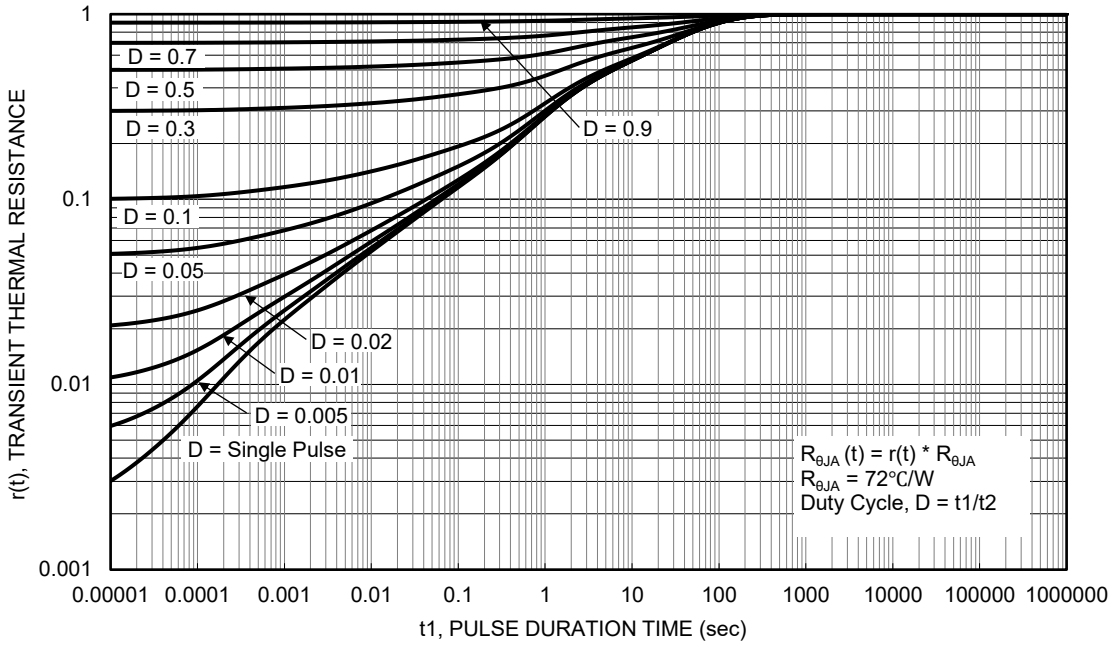
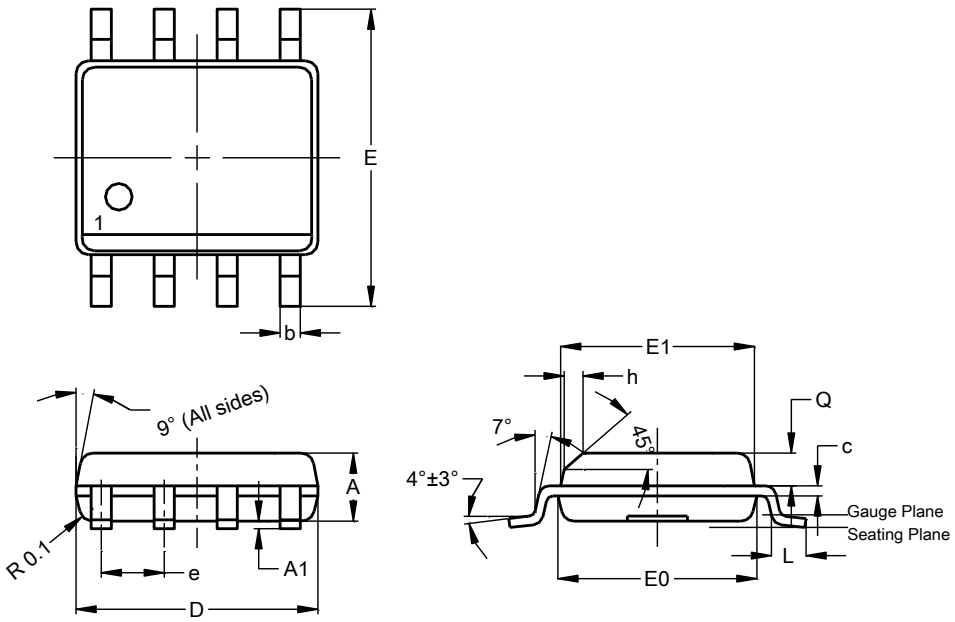


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8

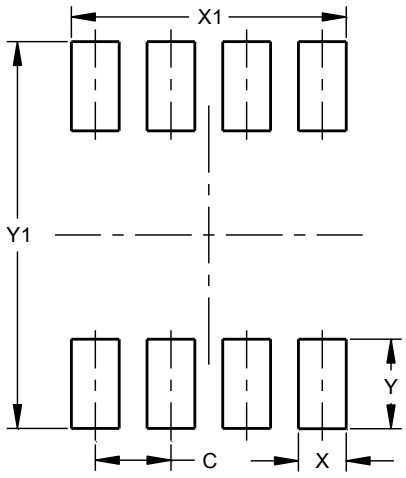


SO-8			
Dim	**Min**	**Max**	**Typ**
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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